

HSU285

Silicon Schottky Barrier Diode for High frequency detection

REJ03G0009-0100Z Rev.1.00 Apr.16.2003

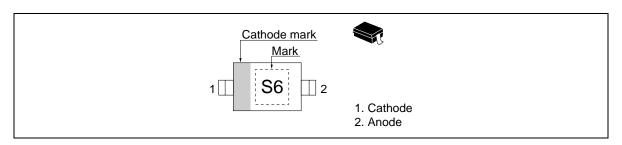
Features

- Low forward voltage, Low capacitance and High detection sensitivity.
- Ultra small Resin Package (URP) is suitable for surface mount design.

Ordering Information

| Type No. | Laser Mark | Package Code |
|----------|------------|--------------|
| HSU285 | S6 | URP |

Pin Arrangement



Datasheet Title<Header>

Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

| Item | Symbol | Value | Unit |
|---------------------------|----------------|-------------|------|
| Reverse voltage | V_R | 2 | V |
| Average rectified current | I _o | 5 | mA |
| Junction temperature | Tj | 125 | °C |
| Storage temperature | Tstg | -55 to +125 | °C |

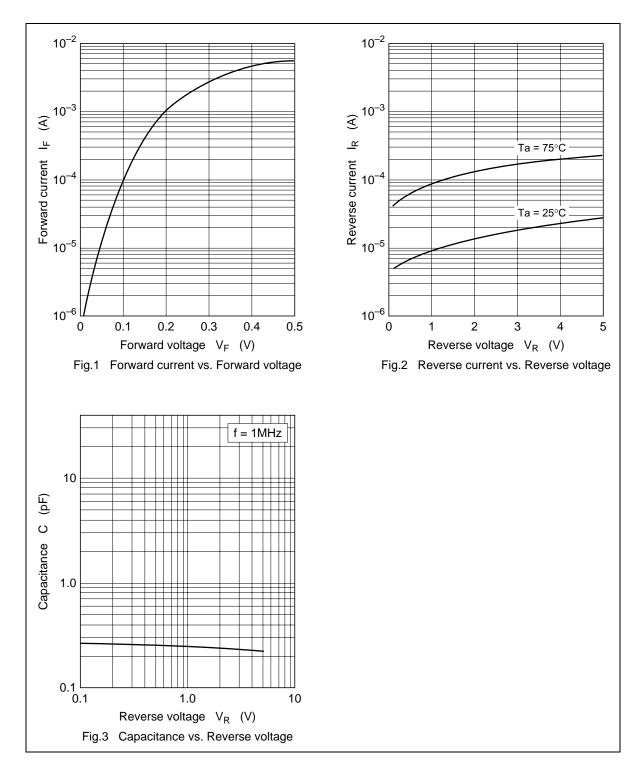
Electrical Characteristics

 $(Ta = 25^{\circ}C)$

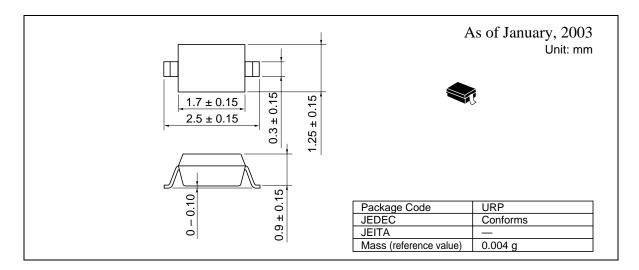
| Item | Symbol | Min | Тур | Max | Unit | Test Condition |
|-------------------|-----------------|-----|-----|------|-------------|--|
| Forward voltage | V_{F1} | _ | _ | 0.15 | V | $I_{F} = 0.1 \text{ mA}$ |
| | V _{F2} | _ | | 0.27 | | I _F = 1 mA |
| Capacitance | С | _ | 0.3 | _ | рF | $V_R = 1 \text{ V}, f = 1 \text{ MHz}$ |
| ESD-Capability *1 | _ | 10 | _ | _ | V | C = 200 pF, R_L = 0 Ω , Both forward and reverse direction 1 pulse. |

Note: 1. Failure criterion ; $I_R > 100 \mu A$ at $V_R = 0.5 V$

Main Characteristic



Package Dimensions



Renesas Technology Corp. Sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

Keep safety first in your circuit designs!

1. Renessa Technology Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage.

Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

Notes regarding these materials

- Notes regarding these materials

 1. These materials are intended as a reference to assist our customers in the selection of the Renesas Technology Corporation product best suited to the customer's application; they do not convey any license under any intellectual property rights, or any other rights, belonging to Renesas Technology Corporation or a third party.

 2. Renesas Technology Corporation assumes no responsibility for any damage, or infringement of any third-party's rights, originating in the use of any product data, diagrams, charts, programs, algorithms, or circuit application examples contained in these materials, including product data, diagrams, charts, programs and algorithms represents information on products at the time of publication of these materials, and are subject to change by Renesas Technology Corporation without notice due to product improvements or other reasons. It is therefore recommended that customers contact Renesas Technology Corporation or an authorized Renesas Technology Corporation product distributor for the latest product information before purchasing a product listed herein.

 The information described here may contain technical inaccuracies or typographical errors.

 Renesas Technology Corporation assumes no responsibility for any damage, liability, or other loss rising from these inaccuracies or errors.

 Please also pay attention to information published by Renesas Technology Corporation by various means, including the Renesas Technology Corporation Semiconductor home page (http://www.renesas.com).

 4. When using any or all of the information contained in these materials, including product data, diagrams, charts, programs, and algorithms, please be sure to evaluate all information as a total system before making a final decision on the applicability of the information and products. Renesas Technology Corporation assumes no responsibility for any damage, liability or other loss resulting from the information contained herein.

 5. Renesas Technology Corporation semiconductors

- 5. Refriesa February Composition Serificultural Ser

- Any diversion or reexport contrary to the export control laws and regulations of Japan and/or the country of destination is prohibited. 8. Please contact Renesas Technology Corporation for further details on these materials or the products contained therein.



http://www.renesas.com

Copyright © 2003. Renesas Technology Corporation, All rights reserved. Printed in Japan.

